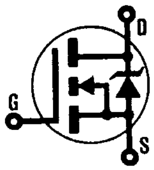
Data Sheet No. PD-9.376G
T-39-13

INTERNATIONAL RECTIFIER IOR

REPETITIVE AVALANCHE AND dv/dt RATED*

HEXFET® TRANSISTORS



N-CHANNEL

IRF840
IRF841
IRF842
IRF843

TO-220

500 Volt, 0.85 Ohm HEXFET
TO-220AB Plastic Package

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of this latest "State of the Art" design achieves: very low on-state resistance combined with high transconductance; superior reverse energy and diode recovery dv/dt capability.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

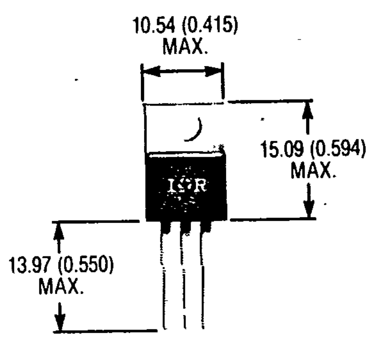
Product Summary

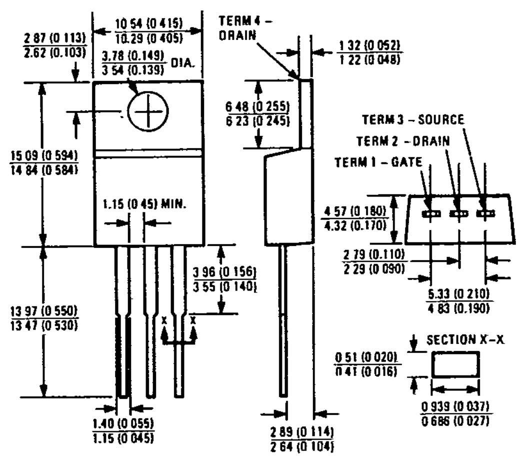
Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRF840	500V	0.85Ω	8.0A
IRF841	450V	0.85Ω	8.0A
IRF842	500V	1.1Ω	7.0A
IRF843	450V	1.1Ω	7.0A

FEATURES:

- Repetitive Avalanche Ratings
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling

CASE STYLE AND DIMENSIONS





Case Style TO-220AB
Dimensions in Millimeters and (Inches)

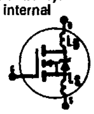
*This data sheet applies to product with batch codes that begin with a digit, ie. 2A3B

IRF840, IRF841, IRF842, IRF843 Devices

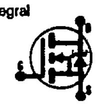
Absolute Maximum Ratings

Parameter		IRF840, IRF841	IRF842, IRF843	Units
I_D @ T_C = 25°C	Continuous Drain Current	8.0	7.0	A
I_D @ T_C = 100°C	Continuous Drain Current	5.1	4.4	A
I_{DM}	Pulsed Drain Current ①	32	28	A
P_D @ T_C = 25°C	Max. Power Dissipation	125		W
	Linear Derating Factor	1.0		W/K ⑤
V_{GS}	Gate-to-Source Voltage	±20		V
E_{AS}	Single Pulse Avalanche Energy ②	510 (See Fig. 14)		mJ
I_{AR}	Avalanche Current ① (Repetitive or Non-Repetitive)	8.0 (See E_{AR})		A
E_{AR}	Repetitive Avalanche Energy ①	13 (See I_{AR})		mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.5 (See Fig. 17)		V/ns
T_J T_{STG}	Operating Junction Storage Temperature Range	−55 to 150		°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		°C

Electrical Characteristics @ T_J = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	IRF840 IRF842	500	—	—	V	V_{GS} = 0V, I_D = 250 μA
		IRF841 IRF843	450				
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance ④	IRF840 IRF841	—	0.70	0.85	Ω	V_{GS} = 10V, I_D = 4.4A
		IRF842 IRF843	—	0.85	1.1		
$I_{D(on)}$	On-State Drain Current ④	IRF840 IRF841	8.0	—	—	A	V_{DS} > $I_{D(on)}$ X $R_{DS(on)}$ Max. V_{GS} = 10V
		IRF842 IRF843	7.0				
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance ④	ALL	4.9	7.4	—	S(℧)	V_{DS} ≥ 50V, I_{DS} = 4.4A
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			—	—	1000		V_{DS} = 0.8 x Max. Rating V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	ALL	—	—	500	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	ALL	—	—	−500	nA	V_{GS} = −20V
Q_g	Total Gate Charge	ALL	—	42	63	nC	V_{GS} = 10V, I_D = 8.0A
Q_{gs}	Gate-to-Source Charge	ALL	—	6.2	9.3	nC	V_{DS} = 0.8 x Max. Rating See Fig. 16
Q_{gd}	Gate-to-Drain ("Miller") Charge		—	22	32	nC	(Independent of operating temperature)
$t_{d(on)}$	Turn-On Delay Time	ALL	—	14	21	ns	V_{DD} = 250V, I_D ≈ 8.0A, R_G = 9.1Ω
t_r	Rise Time	ALL	—	23	35	ns	R_D = 30Ω
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	49	74	ns	See Fig. 15
t_f	Fall Time	ALL	—	20	30	ns	(Independent of operating temperature)
L_D	Internal Drain Inductance	ALL	—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die. — Modified MOSFET symbol showing the internal inductances. 
L_S	Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.
C_{iss}	Input Capacitance	ALL	—	1300	—	pF	V_{GS} = 0V, V_{DS} = 25V
C_{oss}	Output Capacitance	ALL	—	180	—	pF	f = 1.0 MHz
C_{rss}	Reverse Transfer Capacitance	ALL	—	45	—	pF	See Fig. 10

Source-Drain Diode Ratings and Characteristics

	Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	ALL	—	—	8.0	A	Modified MOSFET symbol showing the integral Reverse p-n junction rectifier. 
I_{SM}	Pulsed Source Current (Body Diode) ①	ALL	—	—	32	A	
V_{SD}	Diode Forward Voltage ④	ALL	—	—	2.0	V	T_J = 25°C, I_S = 8.0A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	210	460	970	ns	T_J = 25°C, I_F = 8.0A, di/dt = 100 A/μs
Q_{RR}	Reverse Recovery Charge	ALL	2.0	4.2	8.2	μC	
t_{on}	Forward Turn-On Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	—	—	1.0	K/W ⑤	
R_{thCS}	Case-to-Sink	ALL	—	0.50	—	K/W ⑤	Mounting surface flat, smooth, and greased
R_{thJA}	Junction-to-Ambient	ALL	—	—	80	K/W ⑤	Typical socket mount

TO-220

Typical SPICE Computer Model Parameters (For more information See Application Note AN-975)

Device	Level, SPICE MOSFET Model	W (m), Channel Width	L (μm), Channel Length	Theta (1/V), Mobility Modulation	UO (CM^2/V-S), Surface Mobility	VTO (V), Threshold Voltage	R1 (Ω), Drain Resistance	R2 (Ω), Source Resistance	RG (Ω), Gate Resistance
ALL	3	0.978	1.2	0.20	450	4.27	0.60	0.02	0.5

CGSO (pf), Gate-Source Capacitance	CGD (F) Gate-Drain Capacitance	E1 (V), Voltage Dependent Voltage Source	LD (nH), Drain Inductance	LS (nH), Source Inductance	LG (nH), Gate Inductance	IS (A), Diode Saturation Current	RS (Ω), Diode Bulk Resistance
820	C11	2 + 0.995 VDG	4.5	7.5	7.5	1.3×10^{-12}	0.011

C11 = 3000 pf + 7×10^{-22} $(V_{GE})^{48}$

① Repetitive Rating; Pulse width limited by maximum junction temperature (see figure 5) Refer to current HEXFET reliability report

② @ V_{DD} = 50V, Starting T_J = 25°C, L = 14 mH, R_G = 25Ω, Peak I_L = 8.0A.

③ $I_{SD} \leq$ 8.0A, di/dt $\leq$ 100 A/μs, $V_{DD} \leq BV_{DSS}$, $T_J \leq$ 150°C Suggested R_G = 9.1Ω

④ Pulse width $\leq$ 300 μs; Duty Cycle $\leq$ 2%

⑤ K/W = °C/W W/K = W/°C

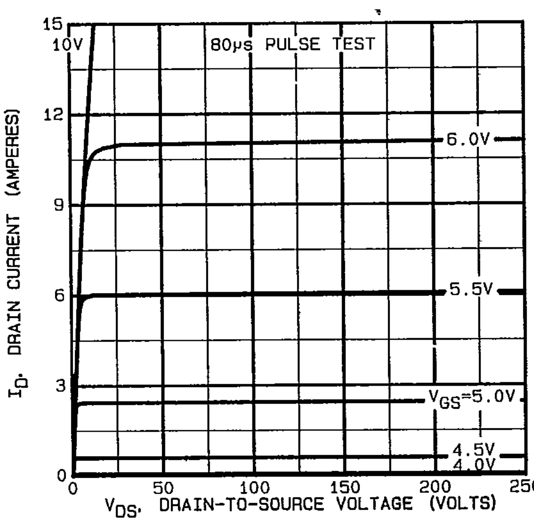


Fig. 1 — Typical Output Characteristics

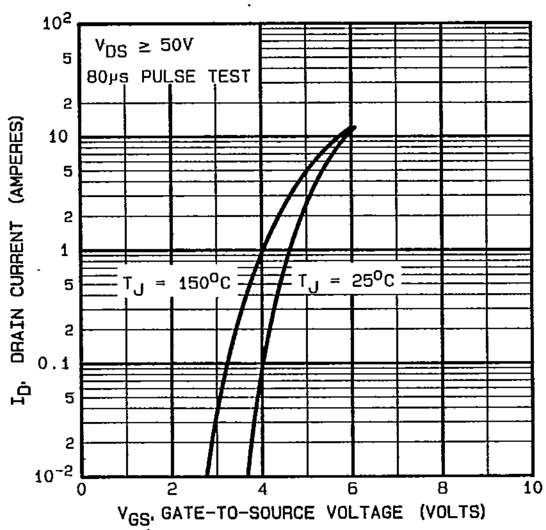


Fig. 2 — Typical Transfer Characteristics

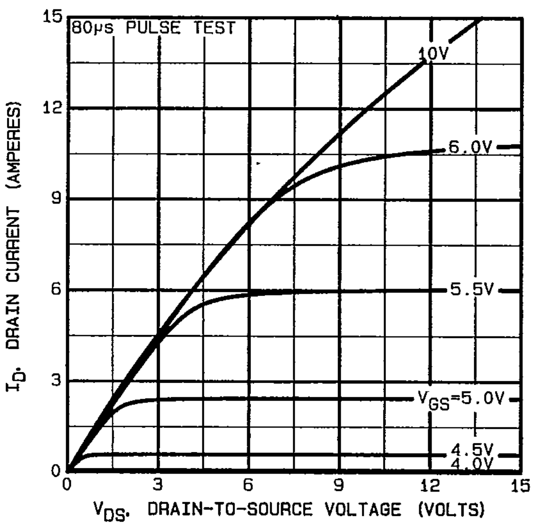


Fig. 3 — Typical Saturation Characteristics

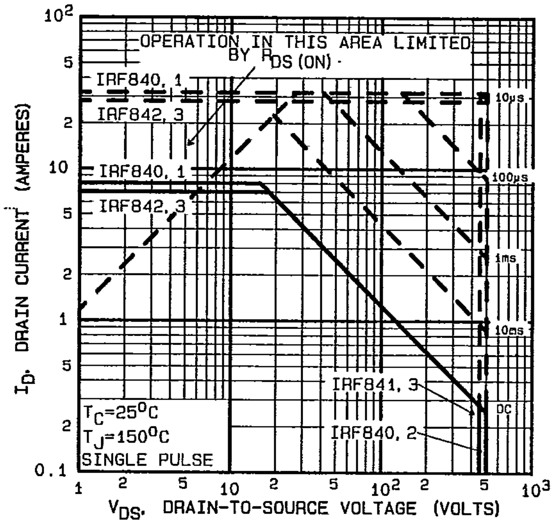


Fig. 4 — Maximum Safe Operating Area

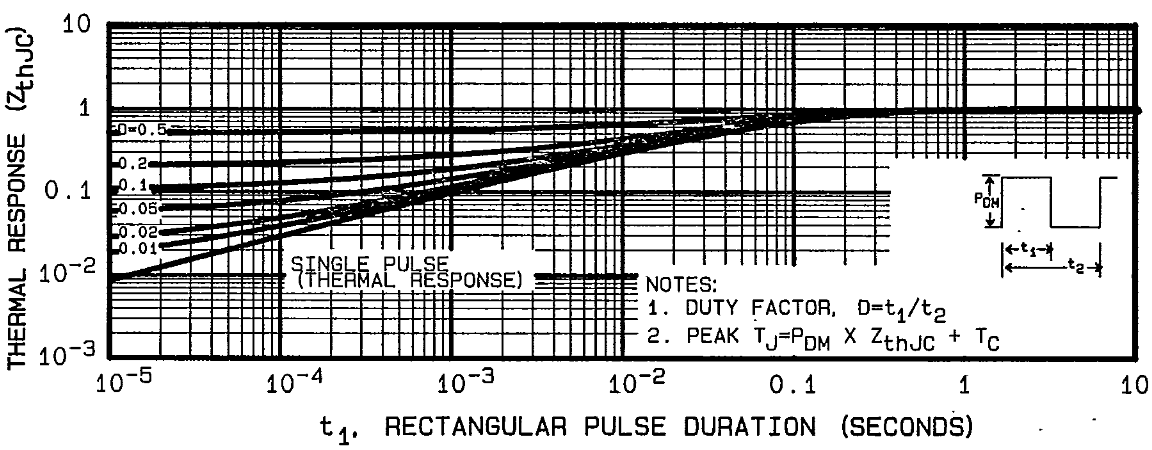


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

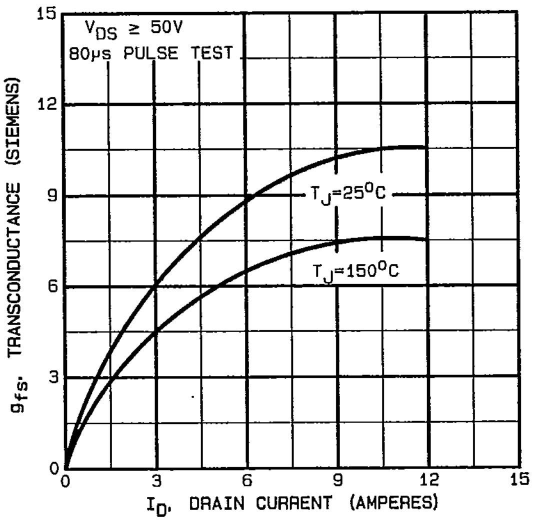


Fig. 6 — Typical Transconductance Vs. Drain Current

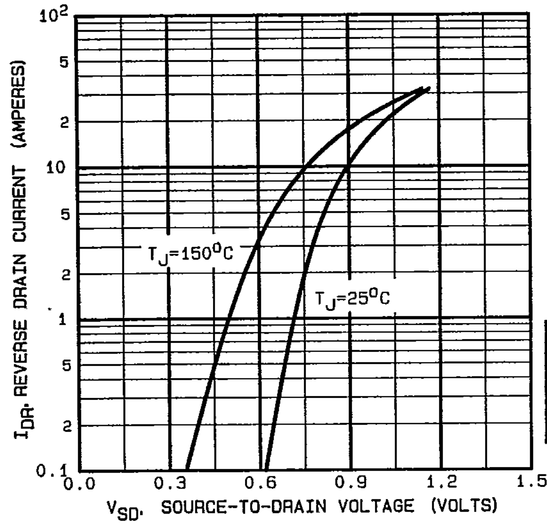


Fig. 7 — Typical Source-Drain Diode Forward Voltage

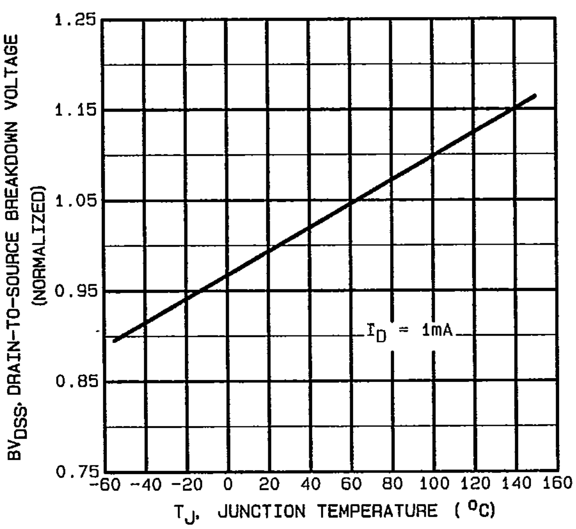


Fig. 8 — Breakdown Voltage Vs. Temperature

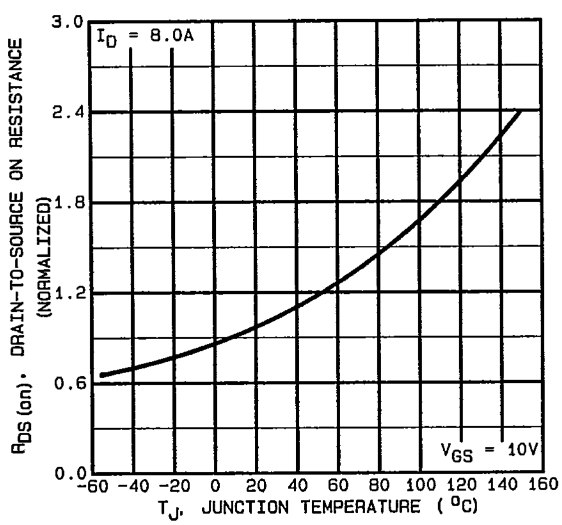


Fig 9 — Normalized On-Resistance Vs. Temperature

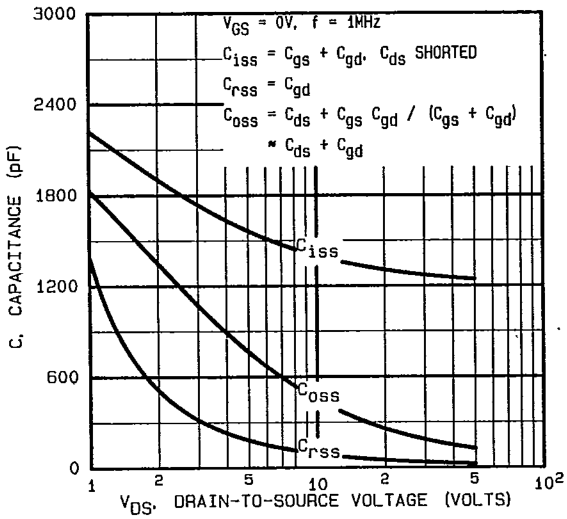


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

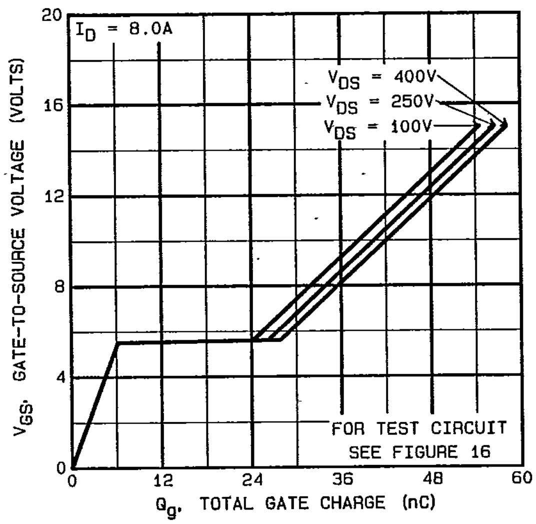


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

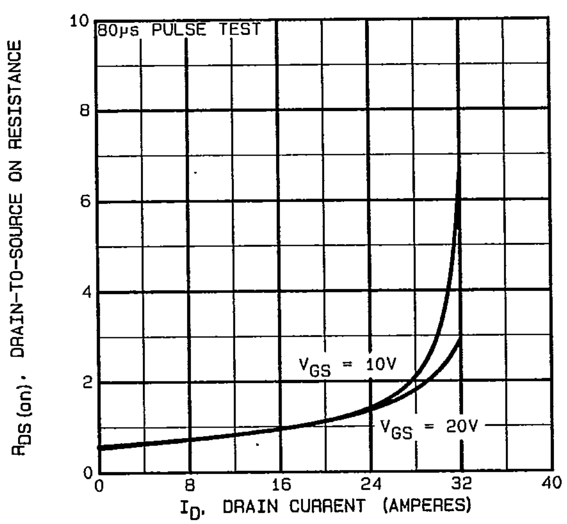


Fig. 12 — Typical On-Resistance Vs. Drain Current

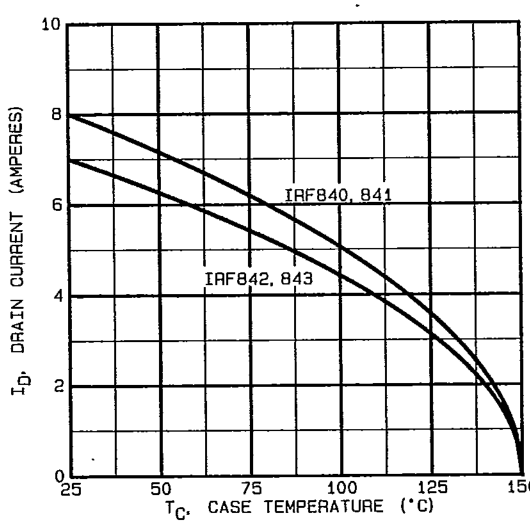


Fig. 13 — Maximum Drain Current Vs. Case Temperature

IRF840, IRF841, IRF842, IRF843 Devices

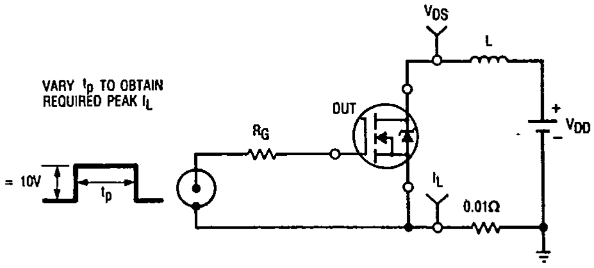


Fig. 14a — Unclamped Inductive Test Circuit

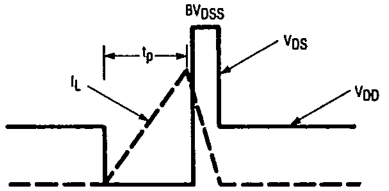
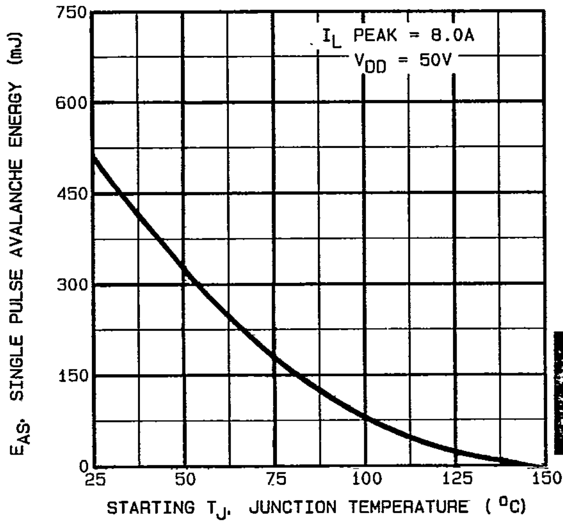


Fig. 14b — Unclamped Inductive Waveforms



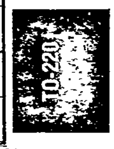


Fig. 14c — Maximum Avalanche Energy Vs. Starting Junction Temperature

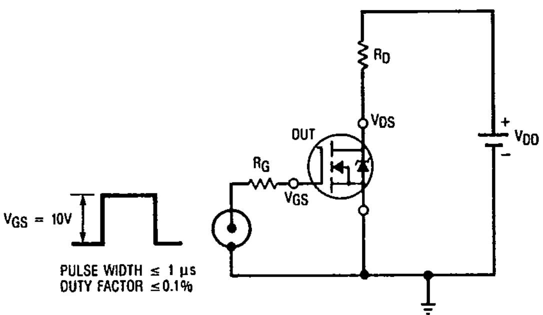


Fig. 15a — Switching Time Test Circuit

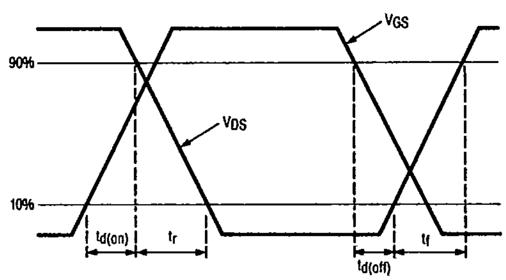


Fig. 15b — Switching Time Waveforms

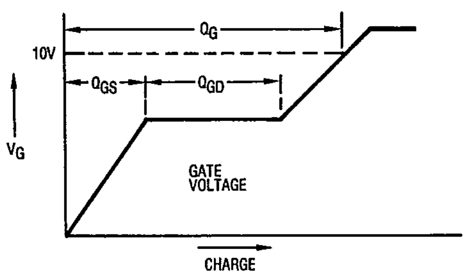


Fig. 16a — Basic Gate Charge Waveform

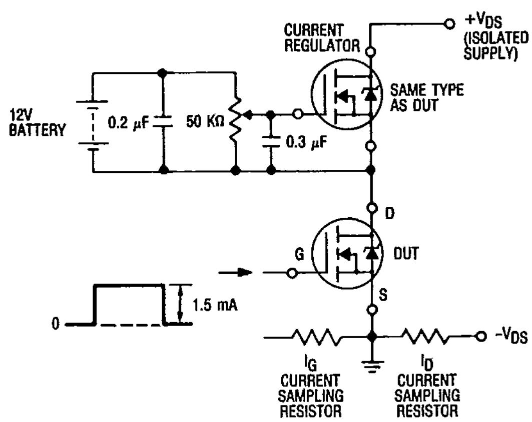


Fig. 16b — Gate Charge Test Circuit

IRF840, IRF841, IRF842, IRF843 Devices

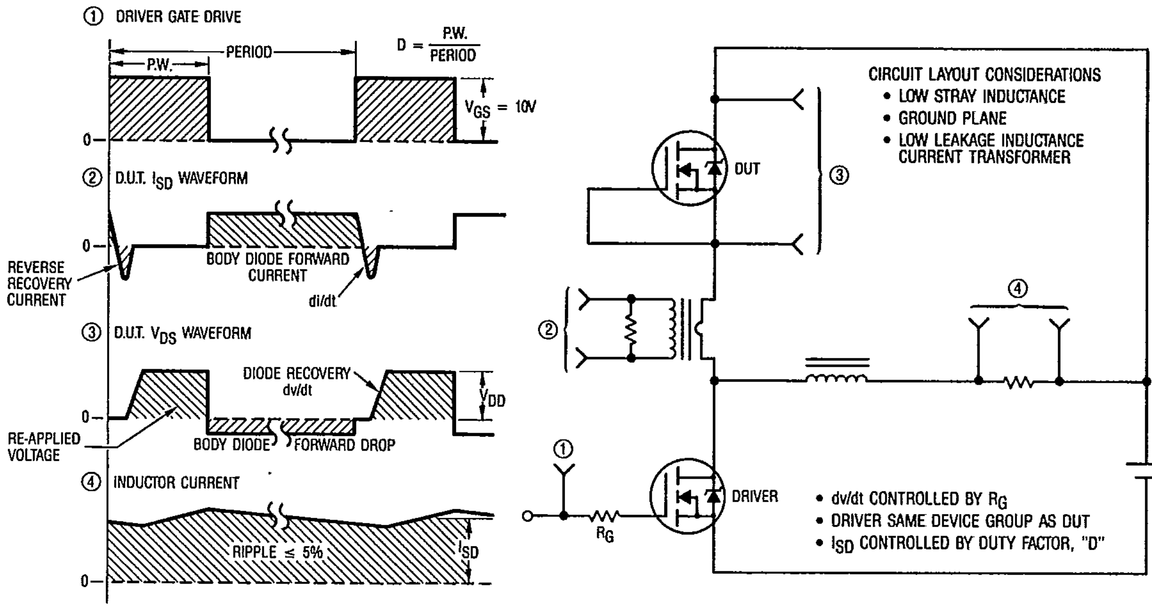


Fig. 17 — Peak Diode Recovery dv/dt Test Circuit

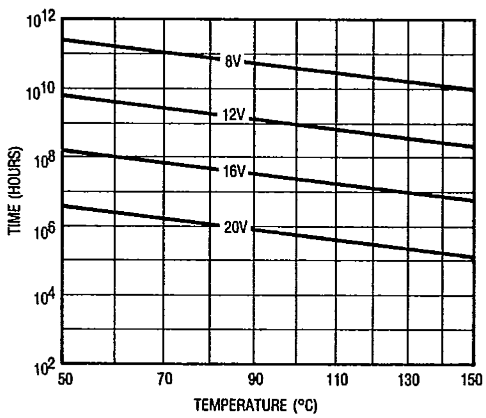


***Fig. 18 — Typical Time to Accumulated 1% Gate Failure**

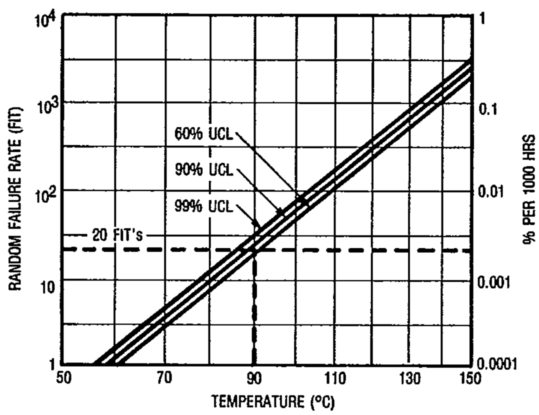


***Fig. 19 — Typical High Temperature Reverse Bias (HTRB) Failure Rate**

*The data shown is correct as of April 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.